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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of: Melvin K. CARTER

Confirmation No: 4809

Serial No: 10/689,616

Group: 1746

Filed: October 22, 2003

Examiner: S. Carrillo

Entitled: **COMPOSITION FOR EXFOLIATION
AGENT EFFECTIVE IN REMOVING
RESIST** Atty Docket: 60937-0141

INFORMATION DISCLOSURE STATEMENT

U.S. Patent and Trademark Office
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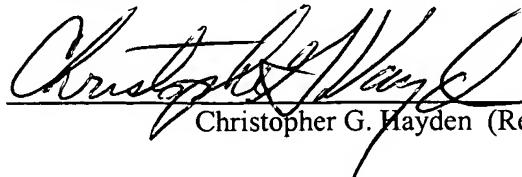
Sir:

In accordance with the duty of disclosure provisions of 37 C.F.R. §1.56, there is hereby provided certain information which the Examiner may consider material to the examination of the subject U.S. patent application. It is requested that the Examiner make this information of record if it is deemed material to the examination of the application.

Enclosed with this Information Disclosure Statement is a list of all patents, publications, applications, or other information submitted for consideration by the Office. There are twenty-eight (28) references listed in the above-referenced application; no U.S. references are submitted, however, the three (3) foreign references, and seven (7) articles are submitted herewith. Remaining references can be provided upon request.

No fee is believed to be due for this submission, since this Information Disclosure Statement is being submitted before the first Office Action. Should any fees be required, however, please charge the required fees to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310

Respectfully submitted,


44,750
Christopher G. Hayden (Reg. No.)

Date December 16, 2004

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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

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C02	Ireland, P., Thin Solid Films, 304, pp. 1-12 (1997)
C03	K. Ueno et al., "Cleaning of CHF ₃ Plasma-Etched SiO ₂ /SiN/Cu Via Structures with Dilute Hydrofluoric Acid Solutions," J. Electrochem. Soc., vol. 144(7), 1997.
C04	Ohman et al., J. Chem. Soc., Dalton Trans. (1983), p. 2513).
C05	Kujime, T. et al., Proc. of the 1996 Semi. Pure Water and Chemicals, pp. 245-256,
C06	Baklanov, M.R. et al., Proc. Electrochem. Soc., 1998, 97-35, pp. 602-609.
C07	Lee, C. and Lee, S, Solid State Electronics, 4, pp. 92 1-923 (1997)
C08	NSF/SRC Eng. Res. Center, Environmentally Benign Semiconductor Manufacturing, Aug. 5-7, 1998, Stanford University. (no publication)
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EXAMINER	DATE CONSIDERED
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)	ATTY DOCKET NO.	APPLICATION NO
	060937-0141-US	10/689,616
	APPLICANT	
	Melvin K. CARTER	
	FILING DATE	GROUP
	October 22, 2003	1746

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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A02	4,395,479	07/1983	Ward et al.			
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B02	WO 98 02794	01/1998	PCT				
B03	9-197681	07/1997	Japan				
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B05							